



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-323 Plastic-Encapsulate DIODE

BAS19W/20W/21W SWITCHING DIODE

FEATURES

Power dissipation

P_D : 200 mW ($T_{amb}=25^{\circ}C$)

Collector current

I_F : 200 mA

Collector-base voltage

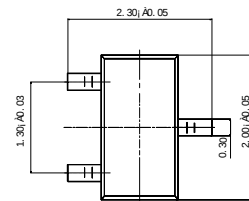
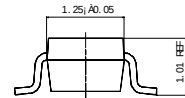
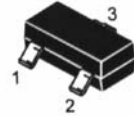
V_R : 19W: 120 V; 20W: 150V ; 21W: 200V

Operating and storage junction temperature range

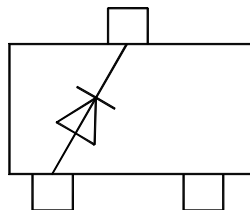
T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-323

1. BASE
2. EMITTER
3. COLLECTOR



Unit: mm



Marking: BAS19W KA8
BAS20W KT2
BAS21W KT3

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage BAS19W BAS20W BAS21W	$V_{(BR)R}$	$I_R=100\mu A$	100 150 200		V
Reverse voltage leakage current BAS19W BAS20W BAS21W	I_R	100V $V_R=150V$ 200V		0.1	μA
Forward voltage	V_F	$I_F=100mA$ $I_F=200mA$		1000 1250	mV
Diode capacitance	C_D	$V_R=0V, f=1MHz$		5	pF
Reveres recovery time	t_{rr}	$I_F=I_R=30mA$ $I_{rr}=0.1 \times I_R$		50	nS